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(74) Agent: **DRAKE, Paul, S.**; Advanced Micro Devices, Inc.,
5204 East Ben White Boulevard, Mail Stop 562, Austin,
TX 78741 (US).

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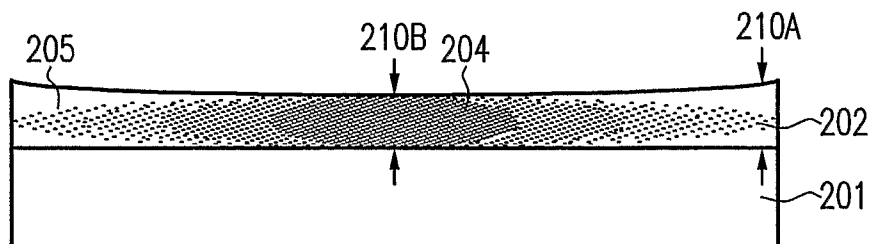
(71) Applicant: **ADVANCED MICRO DEVICES, INC.**
[US/US]; One AMD Place, Mail Stop 68, P.O. Box 3453,
Sunnyvale, CA 94088-3453 (US).

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(72) Inventors: **WIECZOREK, Karsten**; Am Schulfeld 24,
D-01109 Dresden (DE). **GRAETSCH, Falk**; Selliner
Str. 5b, D-01109 Dresden (DE). **HERRMANN, Lutz**;
Bautzner Str. 115, D-01109 Dresden (DE).

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(54) Title: COMPENSATION FOR HETEROGENEOUS NITROGEN CONCENTRATION IN A NITRIDED SILICON OXIDE LAYER



(57) Abstract: The present invention provides a technique for forming extremely thin insulation layers requiring the incorporation of specified amounts of nitrogen, wherein the effect of nitrogen variations across the substrate surface may be reduced in that during and/or after the nitrogen incorporation an oxidation process is performed. The nitrogen variations lead to a nitrogen concentration dependent oxidation rate and, hence, a nitrogen concentration dependent thickness variation of the insulating layer. In particular, the threshold variations of transistors including the thin insulating layer as a gate insulation layer may effectively be reduced.



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